In the Claims:

Claim 1 (currently amended): A structure situated in a semiconductor die, said structure comprising:

an active shield situated in a silicon substrate, said active shield comprising a salicide layer situated on an active region, said active shield having a first conductivity type;

a passive component situated in an interconnect metal layer in said semiconductor die, said passive component being situated above said active shield;

a salicided active region situated in said silicon substrate, said salicided active region situated adjacent to at least one side of, and formed apart from, said active shield, said salicided active region having a second conductivity type;

wherein said active shield defines an AC ground for said passive component.

Claim 2 (original): The structure of claim 1 further comprising at least one contact, said at least one contact connecting said active shield to a semiconductor die AC ground.

Claim 3 (previously amended): The structure of claim 1 further comprising a well situated in said silicon substrate, said active shield being situated in said well, said well having said second conductivity type.

Claim 4 (original): The structure of claim 1 wherein said active shield comprises a plurality of fingers, each of said plurality of fingers comprising a salicide segment situated on an active segment.

Claim 5 (original): The structure of claim 1 wherein said passive component is an inductor.

Claim 6 (previously amended): The structure of claim 3 wherein said salicided active region is situated in said well.

Claim 7 (original): The structure of claim 1 wherein said salicide layer is selected from the group consisting of titanium silicide, cobalt silicide, and nickel mono-silicide.

Claim 8 (original): The structure of claim 3 wherein said well is connected to a voltage source, said voltage source being greater than or equal to ground voltage, said voltage source having no AC component.

Claim 9 (previously amended): The structure of claim 1 further comprising a well situated in said silicon substrate, said active shield being situated in said well, said well having said first conductivity type.

Claim 10 (currently amended): A structure situated in a semiconductor die, said structure comprising:

a well situated in a substrate, said well having a first conductivity type;

an active shield situated in said well, said active shield comprising a salicide layer situated on an active region in said well, said active shield having a second conductivity type;

a passive component situated in an interconnect metal layer in said semiconductor die, said passive component being situated above said active shield;

a salicided active region situated adjacent to at least one side of, and formed apart from, said active shield, said salicided active region having said first conductivity type, said salicided active region being situated in said well;

wherein said active shield defines an AC ground for said passive component.

Claim 11 (original): The structure of claim 10 further comprising at least one contact, said at least one contact connecting said active shield to a semiconductor die AC ground.

Claim 12 (original): The structure of claim 10 wherein said active shield comprises a plurality of fingers, each of said plurality of fingers comprising a salicide segment situated on an active segment.

Claim 13 (canceled).

Claim 14 (original): The structure of claim 10 wherein said passive component is an inductor.

Claim 15 (previously amended): The structure of claim 10 wherein said salicided active region is connected to a voltage source, said voltage source being greater than or equal to ground voltage, said voltage source having no AC component.

Claim 16 (original): The structure of claim 10 wherein said salicide layer is selected from the group consisting of titanium silicide, cobalt silicide, and nickel mono-silicide.

Claim 17 (currently amended): A structure situated in a semiconductor die, said structure comprising:

a well situated in a substrate, said well having a first conductivity type;

an active shield situated in said well, said active shield comprising a plurality of fingers, each of said plurality of fingers comprising a salicide segment situated on an active segment, said each of said plurality of fingers having a second conductivity type;

a salicided active region situated adjacent to at least one side of, and formed apart from, said active shield, said salicided active region having said first conductivity type, said salicided active region being situated in said well;

a passive component situated in an interconnect metal layer in said semiconductor die, said passive component being situated above said active shield;

wherein said active shield defines an AC ground for said passive component.

Claim 18 (original): The structure of claim 17 further comprising at least one contact, said at least one contact connecting said active shield to a semiconductor die AC ground.

Claim 19 (canceled).

Claim 20 (original): The structure of claim 17 wherein said passive component is an inductor, wherein said plurality of fingers terminate an electric field of said inductor.

Claim 21 (previously amended): The structure of claim 17 wherein said salicided active region is connected to a voltage source, said voltage source being greater than or equal to ground voltage, said voltage source having no AC component.